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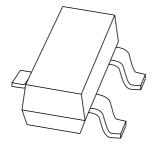
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMMT491A NPN BISS transistor

Product data sheet Supersedes data of 2001 Jun 11 2004 Jan 13



NPN BISS transistor

PMMT491A

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

• Battery powered units where high current and low power consumption are important.

DESCRIPTION

NPN BISS (Breakthrough In Small Signal) transistor in a SOT23 plastic package. PNP complement: PMMT591A.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMMT491A	9A*

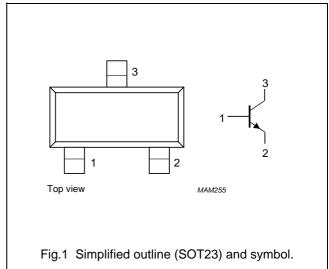
Note

* = p : Made in Hong Kong. * = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE	PACKAGE				
NUMBER	NAME	DESCRIPTION VE			
PMMT491A	_	plastic surface mounted package; 3 leads	SOT23		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	5	٧
I _C	collector current (DC)		_	1	Α
I _{CM}	peak collector current		_	2	А
I _{BM}	peak base current		_	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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NPN BISS transistor

PMMT491A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	100	nA
I _{CEO}	collector cut-off current	I _B = 0; V _{CE} = 30 V	_	100	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	_	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; note 1			
		I _C = 1 mA	300	_	
		$I_{C} = 500 \text{ mA}$	300	900	
		I _C = 1 A	200	_	
V _{CEsat}	collector-emitter saturation voltage	note 1			
		$I_C = 100 \text{ mA}; I_B = 1 \text{ mA}$	_	200	mV
		$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	_	300	mV
		$I_C = 1 A$; $I_B = 100 \text{ mA}$	_	500	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; note 1	_	1.2	V
V _{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 1 A; note 1	_	1.1	V
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	10	pF
f _T	transition frequency	$I_C = 50 \text{ mA}$; $V_{CE} = 10 \text{ V}$; $f = 100 \text{ MHz}$	150	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN BISS transistor

PMMT491A

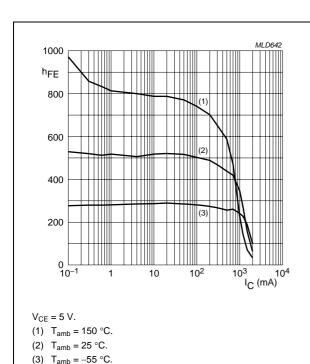
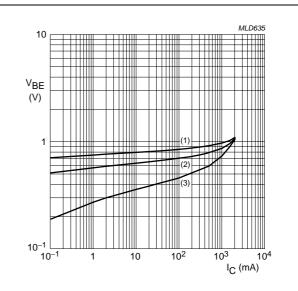


Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 5 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.3 Base-emitter voltage as a function of collector current; typical values.

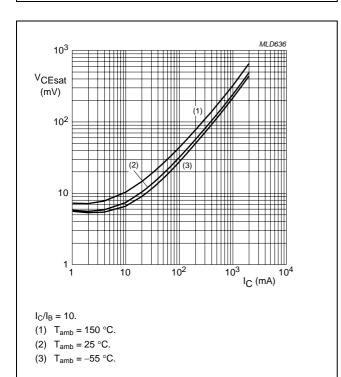
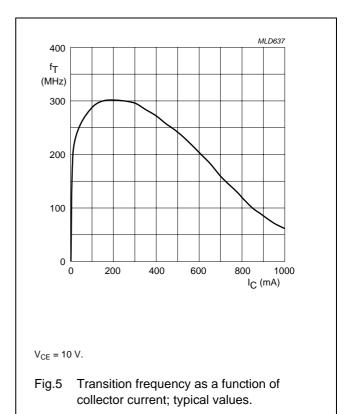


Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



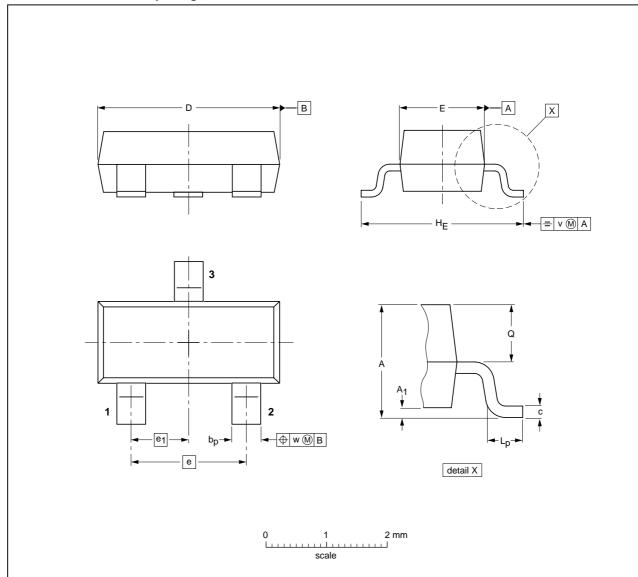
NPN BISS transistor

PMMT491A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

ι	JNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
	mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04 06-03-16

NPN BISS transistor

PMMT491A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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